IN THE CLAIMS

1.-2.(canceled)

3. (currently amended): ~~The semiconductor apparatus according to claim 1, further comprising~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material;

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer; and

a first interdielectric layer disposed between said substrate and said adhesion layer.

4. (original): The semiconductor apparatus according to claim 3, wherein said first interdielectric layer including at least one of a silicon oxide film and a silicon nitride film.

5.-9. (canceled)

10. (currently amended): ~~The semiconductor apparatus according to claim 1, further comprising~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material;

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer; and

an electrically conductive layer disposed between said adhesion layer and said semiconductor thin film.

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11. (canceled)

12. (currently amended): ~~The semiconductor apparatus according to claim 2, further comprising~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material;

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer; and

an individual interconnecting layer extending from an upper surface of said semiconductor thin film to an upper surface of a terminal area of said integrated circuit so that said semiconductor device and said integrated circuit are electrically connected to each other.

13. (original): The semiconductor apparatus according to claim 12, further comprising a second interdielectric layer which electrically isolates said individual interconnecting layer from said semiconductor thin film and apart of said substrate.

14. (original): The semiconductor apparatus according to claim 13, wherein said second interdielectric layer including at least one of a silicon oxide film and a silicon nitride film.

15. (currently amended): The semiconductor apparatus according to claim [[12,]] 3, further comprising:

an individual interconnecting layer extending from an upper surface of said semiconductor thin film to an upper surface of said substrate; and

an electrode pad disposed on said first interdielectric layer, said electrode pad being electrically connected to said individual interconnecting layer.

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16.-17. (canceled)

18. (currently amended): ~~The semiconductor apparatus according to claim 1,~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material; and

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer;

wherein a number of said at least one semiconductor device is plural, and a plurality of said semiconductor devices are arranged in said semiconductor thin film at regular intervals.

19. (currently amended): ~~The semiconductor apparatus according to claim 1,~~

A semiconductor apparatus comprising:

a substrate;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material; and

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer;

wherein a number of said at least one semiconductor device formed in said semiconductor thin film is one, a number of said at least one semiconductor film is plural, and a plurality of said semiconductor thin films are arranged on said adhesion layer at regular intervals.

20.-25. (canceled)

26. (new): A semiconductor apparatus comprising:

a substrate;

at least one semiconductor thin film including at least one semiconductor device; and

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an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material, a main constituent of said adhesion layer being different from a main constituent of said at least one semiconductor thin film, said semiconductor material having an affinity to both of said at least one semiconductor thin film and said substrate;

said at least one semiconductor thin film being bonded on said adhesion layer.

27. (new): The semiconductor apparatus according to claim 26, wherein said substrate is a semiconductor substrate including an integrated circuit which includes a plurality of circuit elements.

28. (new): The semiconductor apparatus according to claim 27, wherein said semiconductor thin film is disposed on a region of said substrate adjacent to a region in which said integrated circuit is formed.

29. (new): The semiconductor apparatus according to claim 27, wherein said semiconductor thin film is disposed on a region of said substrate in which said integrated circuit is formed.

30. (new): The semiconductor apparatus according to claim 26, wherein said substrate is an insulating substrate.

31. (new): The semiconductor apparatus according to claim 26, wherein said adhesion layer is any of a polycrystalline silicon layer and an amorphous silicon layer;

wherein said semiconductor thin film is a compound semiconductor thin film;

wherein amain constituent of said substrate is different from a main constituent of said semiconductor thin film.

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32. (new): The semiconductor apparatus according to claim 26, wherein said semiconductor thin film is a compound semiconductor thin film.

33. (new): The semiconductor apparatus according to claim 26, wherein said semiconductor device is any of a light-emitting element, a light-sensing element, a Hall element, and a piezoelectric element.

34. (new): An optical print head including the semiconductor apparatus of claim 26.

35. (new): An optical print head including the semiconductor apparatus of claim 26, wherein the semiconductor device in the thin semiconductor film in the semiconductor apparatus is a light-emitting element, the semiconductor apparatus including a plurality of such light-emitting elements, the optical print head further including:

a base for supporting the semiconductor apparatus;

a rod lens array for focusing the light emitted by the light-emitting elements in the semiconductor apparatus;

a holder for holding the rod lens array; and

at least one clamp for holding the base and the holder together.

36. (new): An image-forming apparatus comprising at least one optical print head including the semiconductor apparatus of claim 26.

37. (new): The image-forming apparatus of claim 36, further comprising:

a photosensitive drum selectively illuminated by the optical printing head to form a latent electrostatic image.

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38. (new): The image-forming apparatus of claim 37, further comprising:

a developing unit for supplying toner to develop the latent electrostatic image on the photosensitive drum; and

a transfer roller for transferring the developed image from the photosensitive drum to printing media.

39. (new): A semiconductor apparatus comprising:

a substrate which is a monolithic Si substrate including an integrated circuit;

an adhesion layer disposed on said substrate, said adhesion layer mainly consisting of semiconductor material; and

at least one semiconductor thin film including at least one semiconductor device, said at least one semiconductor thin film being bonded on said adhesion layer.

I certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office (fax no. 571-273-8300) on November 16, 2005.

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